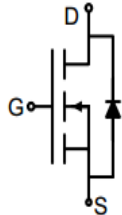
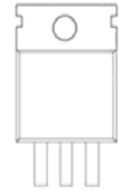


N-Channel Enhancement Mode Power MOSFET

Description The G60N06T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.		 Schematic diagram	
General Features ● V_{DS} 60V ● I_D (at $V_{GS} = 10V$) 50A ● $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 17mΩ ● $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 21mΩ ● 100% Avalanche Tested ● RoHS Compliant		 Marking and pin assignment	
Application ● Power switch ● DC/DC converters		 TO-220	
Device	Package	Marking	Packaging
G60N06T	TO-220	G60N06	50pcs/Tube

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current	I_D	50	A
Pulsed Drain Current (note1)	I_{DM}	200	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D	85	W
Single pulse avalanche energy (note3)	E_{AS}	42	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	°C

Thermal Resistance

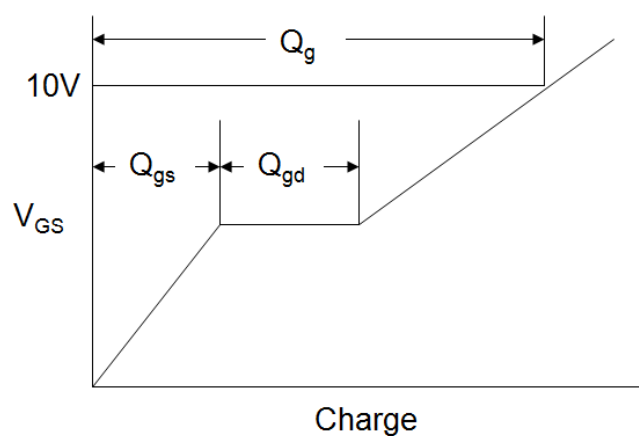
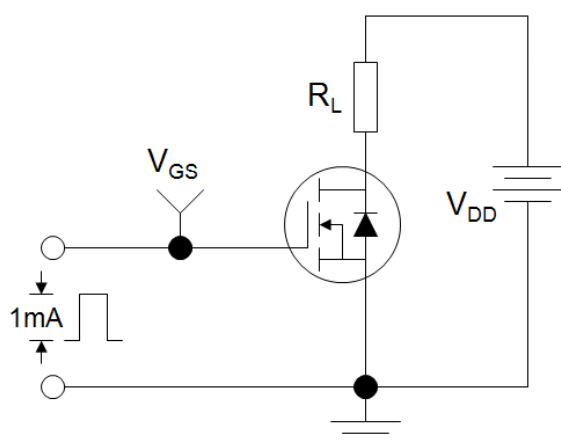
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.8	°C/W

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 5A	--	14	17	mΩ
		V _{GS} = 4.5V, I _D = 3A	--	16	21	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	18	--	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 30V, f = 1.0MHz	--	2050	--	pF
Output Capacitance	C _{oss}		--	158	--	
Reverse Transfer Capacitance	C _{rss}		--	120	--	
Total Gate Charge	Q _g	V _{DD} = 30V, I _D = 20A, V _{GS} = 10V	--	50	--	nC
Gate-Source Charge	Q _{gs}		--	6	--	
Gate-Drain Charge	Q _{gd}		--	15	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 30V, I _D = 20A, R _G = 3Ω	--	7	--	ns
Turn-on Rise Time	t _r		--	5	--	
Turn-off Delay Time	t _{d(off)}		--	28	--	
Turn-off Fall Time	t _f		--	5.5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	50	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 15A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	T _{rr}	I _S = 10A, V _{GS} = 0V di/dt=100A/us	--	28	--	ns

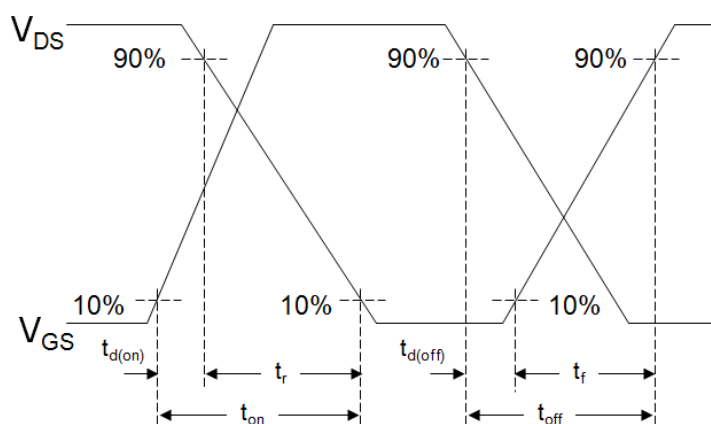
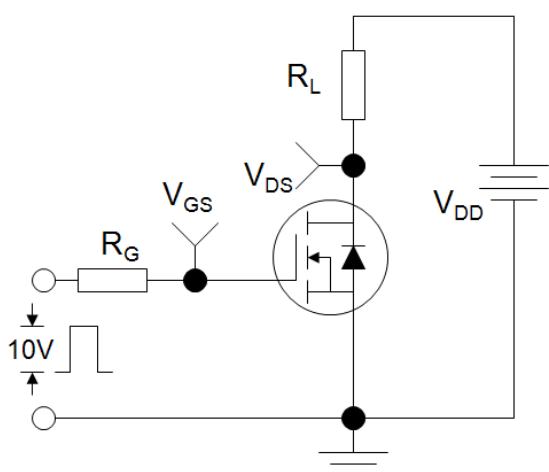
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J=25^{\circ}\text{C}$, $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_g=25\Omega$

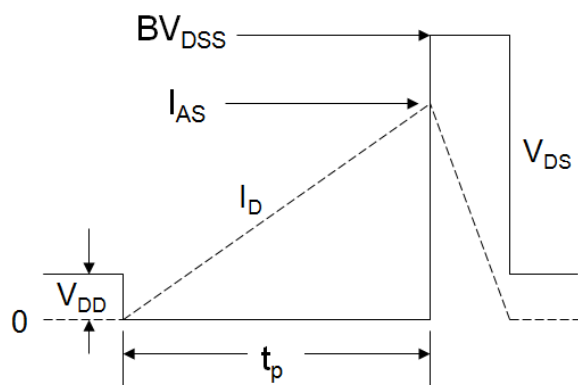
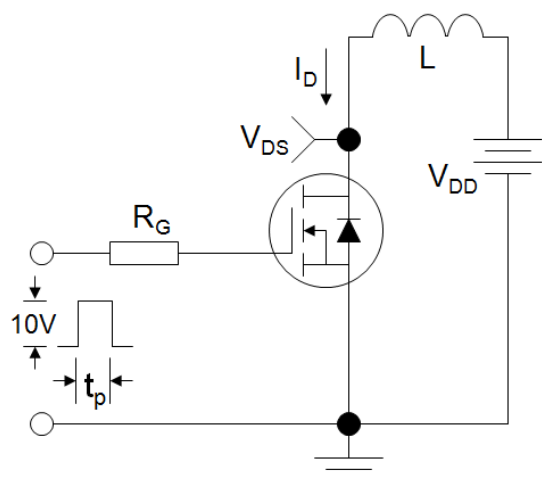
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

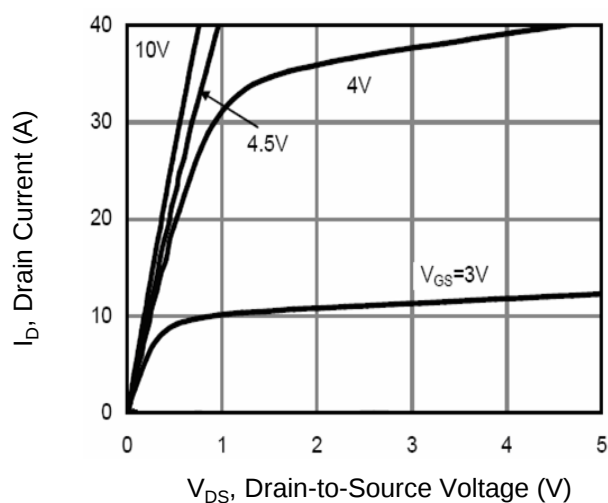


Figure 2. Transfer Characteristics

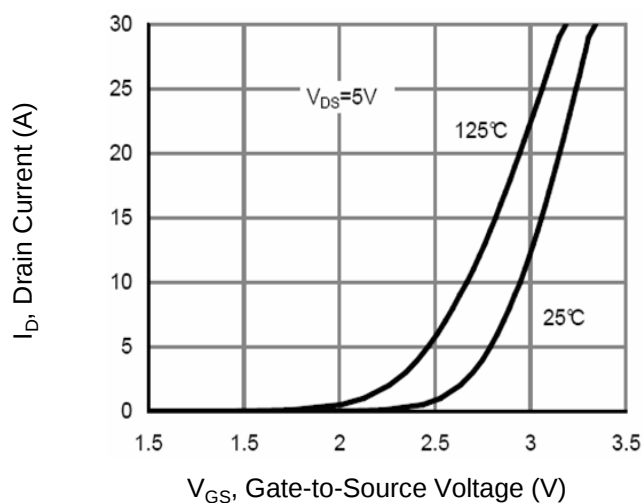


Figure 3. Gate Charge

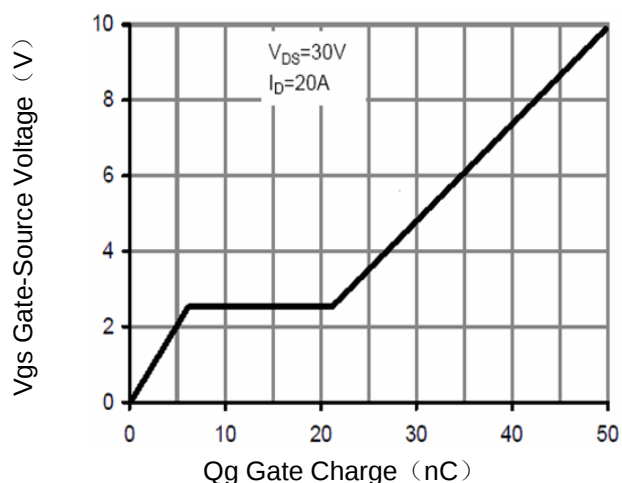


Figure 4. Drain Source On Resistance

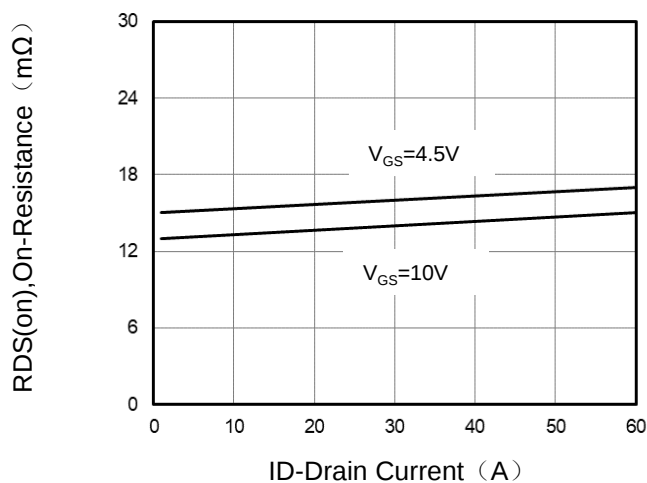


Figure 5. Capacitance

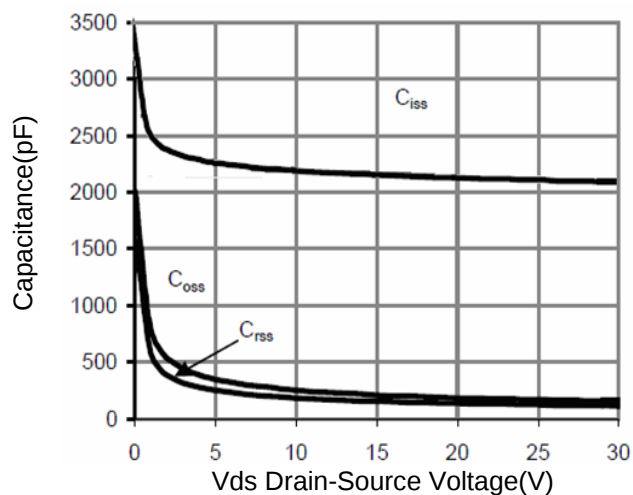
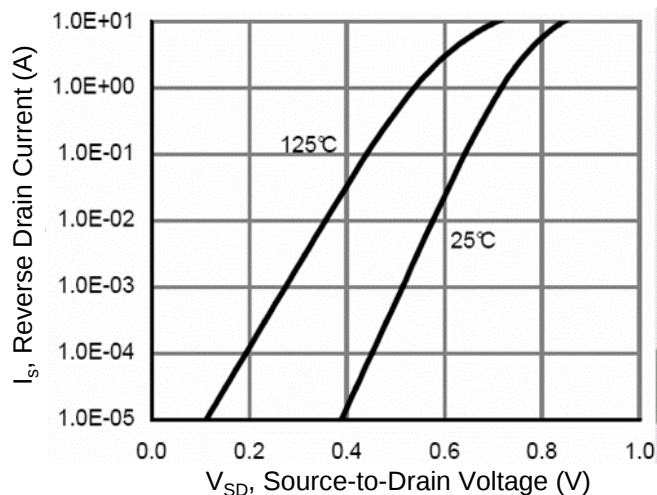


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

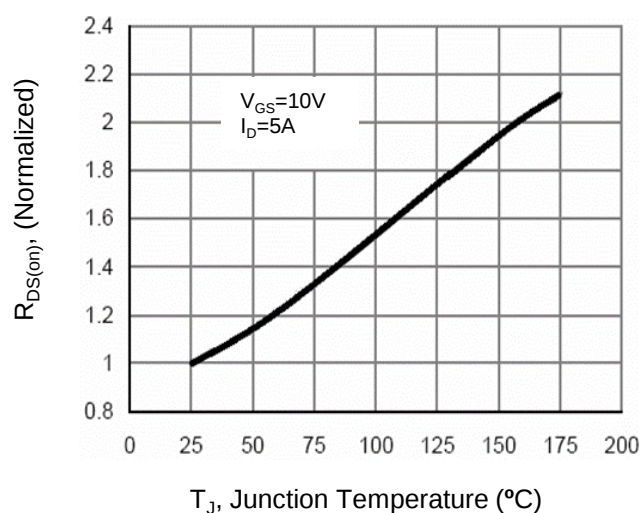


Figure 8. Safe Operation Area

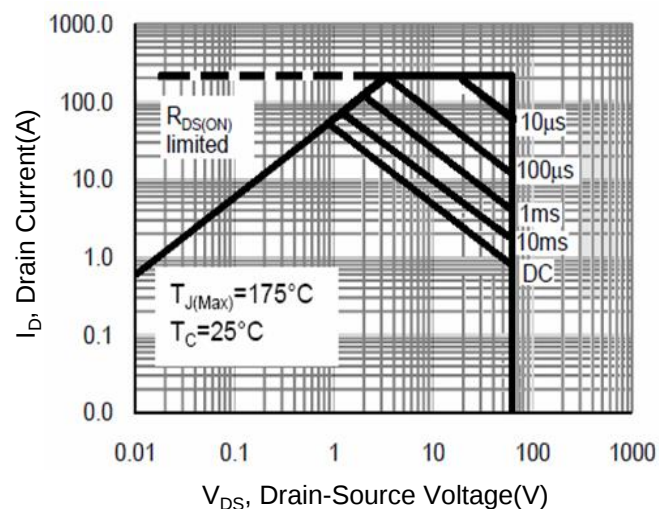
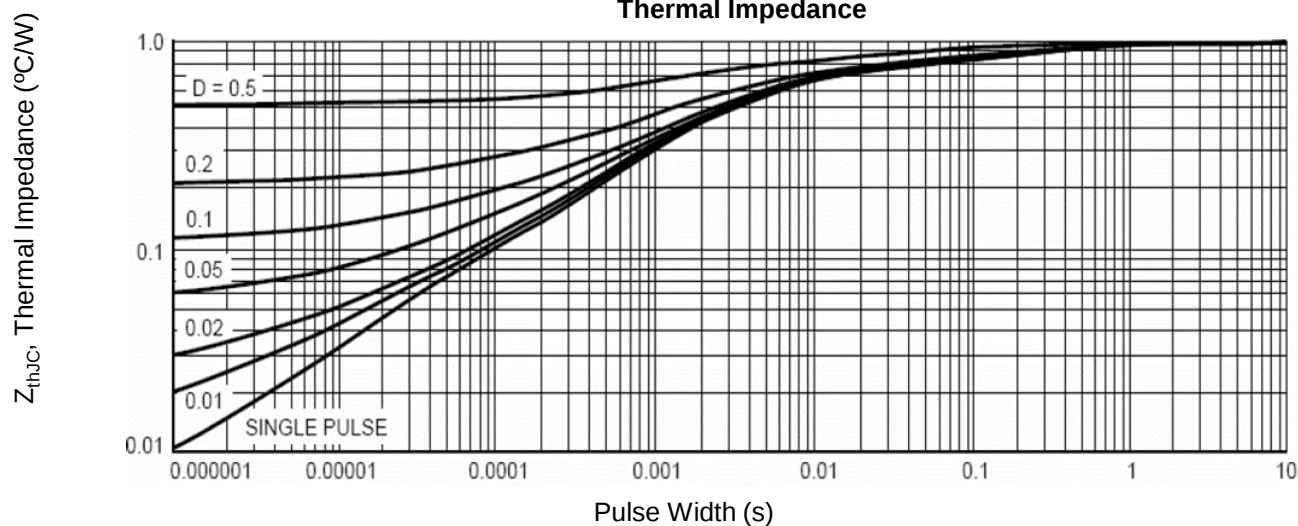
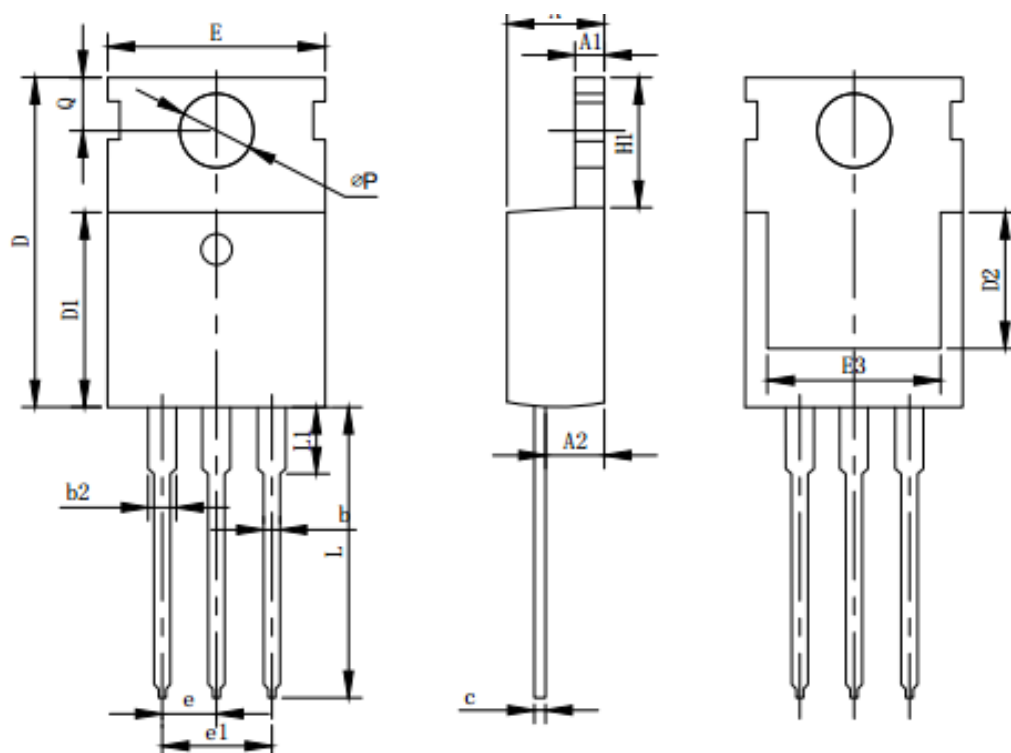


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	4.37	4.57	4.7
A1	1.25	1.3	1.4
A2	2.2	2.4	2.6
b	0.7	0.8	0.95
b2	1.7	1.27	1.47
c	0.45	0.5	0.6
D	15.1	15.6	16.1
D1	8.8	9.1	9.4
D2	5.5		
E	9.7	10	10.3
e	2.54BSC		
e1	5.08BSC		
H1	6.25	6.5	6.85
L	12.75	13.5	13.8
L1		3.1	3.4
øP	3.4	3.6	3.8
Q	2.6	2.8	3